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This invention relates to semiconductor technology and can be used for manufacturing solar radiation-to-electric energy converters.

The pInP-nCdS structure growth method comprises placing a pre-etched pInP substrate with the crystallographic orientation (100) and disorientation of 3…5° in the direction (110) into a reactor, heating the substrate growth zone and stabilizing the temperature in the range of 400…450°C, spraying, in open oxygen flow, the $CdCl_2$ and $SnSl_4$ solutions with the formation on the substrate of a Cd_2SnO_4 layer, then spraying the $CdCl_2$ and $CS(NH_2)_2$ solutions with the formation thereon of a nCdS layer.

Claims: 1